NSN 5961-00-852-2552



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-00-852-2552 **Inclosure Material:** Metal **Overall Length:** 1.252 inches **Overall Height:** 0.340 inches **Overall Width:** 0.700 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 375.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 250.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 5.00 amperes source cutoff current and 1.00 amperes source cutoff current **Power Rating Per Characteristic:** 35.0 watts small-signal input power, common-collector **Transfer Ratio:** 100.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius case **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case

N/a

Unit Of Measure:

Shelf Life:

Specification Data:

80131-release4901 professional/industrial association specification

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